N-Channel 30-V (D-S) MOSFET

Key Features:

- Low r_{DS(on)} trench technology
- · Low thermal impedance
- · Fast switching speed

Typical Applications:

- · White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

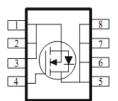
PRODUCT SUMMARY				
V _{DS} (V)	$r_{DS(on)}(m\Omega)$	I⊳(A)		
30	13 @ V _{GS} = 10V	16		
30	20 @ V _{GS} = 4.5V	13		







DFN5X6-8L



ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)							
Parameter	Symbol	Limit	Units				
Drain-Source Voltage			30	V			
Gate-Source Voltage		V_{GS}	±20	V			
Continuous Drain Current a	T _A =25°C	1	16				
Continuous Drain Current	T _A =70°C	I _D	12.8	Α			
Pulsed Drain Current ^b		I _{DM}	50				
Continuous Source Current (Diode Conduction) a		I _S	7.1	Α			
Power Dissipation ^a	T _A =25°C	P_{D}	5	W			
Power Dissipation	T _A =70°C	' D	3.2	V V			
Operating Junction and Storage Temperature Range		T_J,T_stg	-55 to 150	°C			

THERMAL RESISTANCE RATINGS							
Parameter			Maximum	Units			
Maximum Junction-to-Ambient ^a	t <= 10 sec	$R_{\theta JA}$	25	°C/W			
Maximum Junction-to-Ambient	Steady State		65	C/ VV			

1

Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Electrical Characteristics

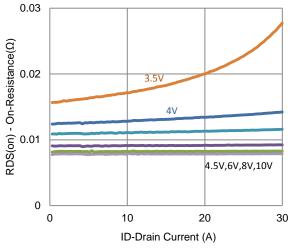
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250 \text{ uA}$	1			V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}$			1	· uA	
Zero Gate Voltage Brain Gurrent	DSS	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			25		
On-State Drain Current	I _{D(on)}	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	20			Α	
Drain-Source On-Resistance	r	$V_{GS} = 10 \text{ V}, I_{D} = 12.8 \text{ A}$			13	mΩ	
Dialii-Source Off-Nesistance	r _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 10.2 \text{ A}$			20		
Forward Transconductance	g _{fs}	$V_{DS} = 15 \text{ V}, I_{D} = 12.8 \text{ A}$		15		S	
Diode Forward Voltage	V_{SD}	$I_S = 3.5 \text{ A}, V_{GS} = 0 \text{ V}$		0.74		V	
		Dynamic					
Total Gate Charge	Q_g	$V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V},$		15			
Gate-Source Charge	Q_{gs}	$I_{DS} = 13 \text{ V}, \text{ V}_{GS} = 4.3 \text{ V},$ $I_{D} = 13.4 \text{ A}$		5.6		nC	
Gate-Drain Charge	Q_{gd}	1D = 10.4 A		7.0			
Turn-On Delay Time	t _{d(on)}			6			
Rise Time	t _r	$V_{DS} = 15 \text{ V}, R_L = 1.2 \Omega, I_D = 12.8 \text{ A},$		15		ns	
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = 10 \text{ V}, R_{GEN} = 6 \Omega$		38			
Fall Time	t _f			20			
Input Capacitance	C _{iss}			1456		_	
Output Capacitance	C _{oss}	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		231		pF	
Reverse Transfer Capacitance	C_{rss}			198			

Notes

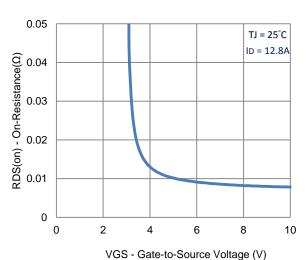
- Pulse test: PW <= 300us duty cycle <= 2%.
- Guaranteed by design, not subject to production testing. b.

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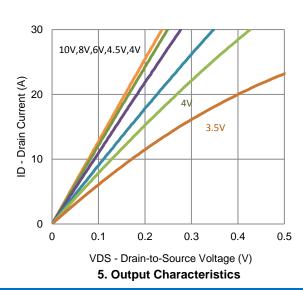
Typical Electrical Characteristics



1. On-Resistance vs. Drain Current



3. On-Resistance vs. Gate-to-Source Voltage



TJ = 25°C

40

40

40

40

20

10

0

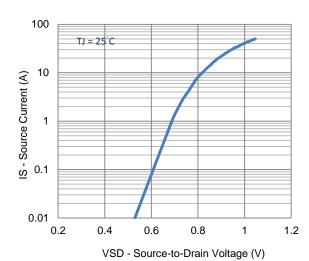
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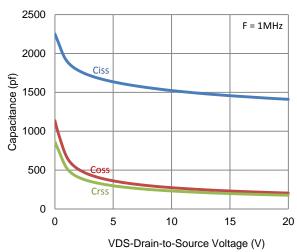
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VGS - Gate-to-Source Voltage (V)

2. Transfer Characteristics



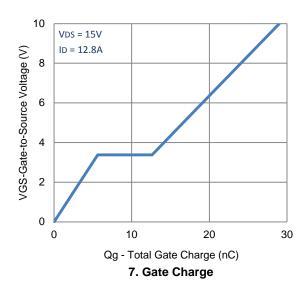
4. Drain-to-Source Forward Voltage

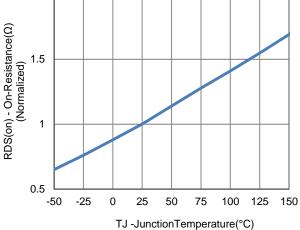


6. Capacitance

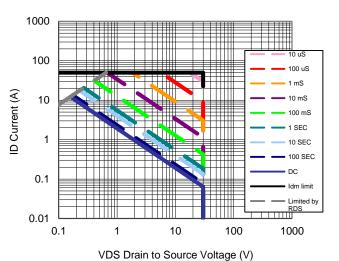
Typical Electrical Characteristics

2

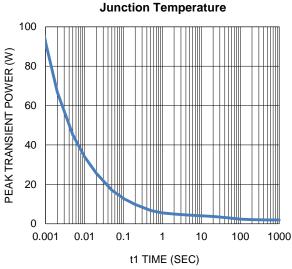




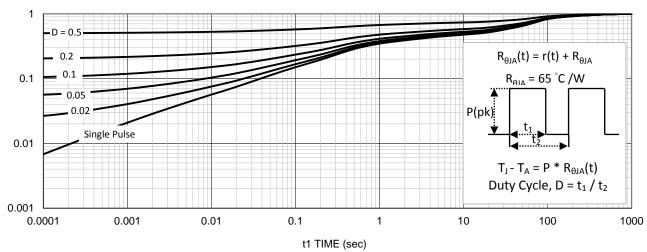
8. Normalized On-Resistance Vs



9. Safe Operating Area

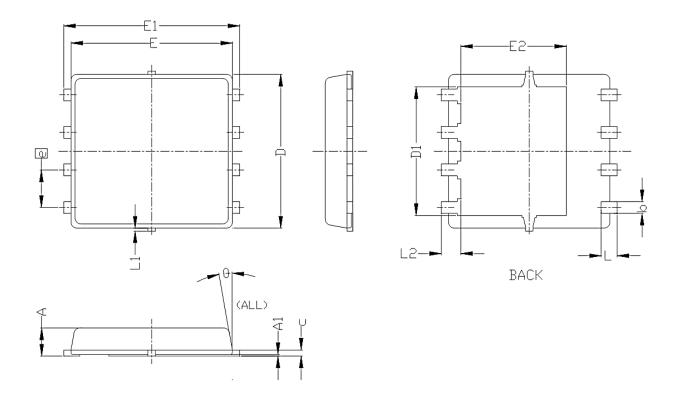


10. Single Pulse Maximum Power Dissipation



11. Normalized Thermal Transient Junction to Ambient

Package Information



SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES			
STMBULS	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0.85	0.95	1.00	0.033	0.037	0.039	
Al	0.00		0.05	0.000		0.002	
b	0.30	0.40	0.50	0.012	0.016	0.020	
c	0.15	0.20	0. 25	0.006	0.008	0.010	
D	5. 20 BSC			0. 205 BSC			
D1	4. 35 BSC				0. 171 BSC		
E	5, 55 BSC			0. 219 BSC			
E1	6. 05 BSC			0. 238 BSC			
E2	3. 62 BSC			0. 143 BSC			
e	1. 27 BSC			0.050 BSC			
L	0.45	0.55	0.65	0.018	0.022	0.026	
L1	0		0.15	0		0.006	
L2	0.68 REF			0.027 REF			
θ	0°		10°	0°		10°	